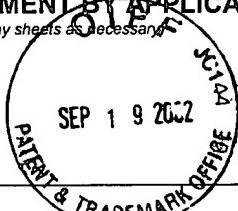


Substitute for form 1449A/PTO

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**
(Use as many sheets as necessary)

Complete if Known

Application Number	09/483881
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First Named Inventor	Ahn, Kie
Group Art Unit	2812
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Sheet 1 of 1

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11-19-02